



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Philip L. Hower, et al. Docket No: TI-30010
Serial No: 10/036,323 Conf. No: 3224
Examiner: Thomas L. Dickey Art Unit: 2826
Filed: 12/31/2001
For: N-CHANNEL LDMOS WITH BURIED P-TYPE REGION TO PREVENT PARASITIC
BIPOLAR EFFECTS

LETTER TO OFFICIAL DRAFTSPERSON

Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Attention: Official Draftsperson

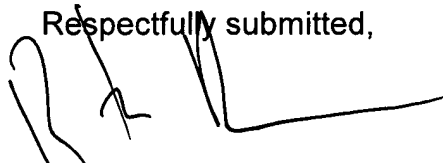
MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(a)
I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 7-18-05.


Ann Trent

Dear Sir:

Transmitted herewith for filing are six replacement sheets of corrected formal drawings for the above identified application. Charge any necessary fees to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.

Respectfully submitted,



Peter K. McLarty
Attorney for Applicants
Reg. No. 44,923

Texas Instruments Incorporated
P.O. Box 655474, MS 3999
Dallas, TX 75265
(972) 917-4258



ATTORNEY: PKM
DOCKET NO: TL30010
DATE: 6-1-5
DUE DATE: 6-2-5

*TEXAS INSTRUMENTS
PATENT DRAFTING*

*Michael Jenkins
972-917-5639*
